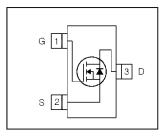


## IRLML0060TRPbF

HEXFET® Power MOSFET

V <sub>DSS</sub>	60	٧
V <sub>GS</sub>	±16	V
R <sub>DS(on)</sub> max (@ V <sub>GS</sub> = 10V)	92	mΩ
$R_{DS(on)}$ max (@ $V_{GS}$ = 4.5V)	116	mΩ





G	D	S
Gate	Drain	Source

## **Applications**

Load/System Switch

### **Features**

Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1

#### **Benefits**

Base part number	part number Package Type Standard Pack		Orderable Part Number	
Dase part number	Fackage Type	Form	Quantity	Olderable Fait Number
IRLML0060TRPbF	Micro 3™ (SOT-23)	Tape and Reel	3000	IRLML0060TRPbF

**Absolute Maximum Ratings** 

Symbol	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	60	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	2.7	
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	2.1	Α
I <sub>DM</sub>	Pulsed Drain Current	11	
P <sub>D</sub> @T <sub>A</sub> = 25°C	Maximum Power Dissipation	1.25	10/
P <sub>D</sub> @T <sub>A</sub> = 70°C	Maximum Power Dissipation	0.80	W
	Linear Derating Factor	0.01	mW/°C
V <sub>GS</sub> Gate-to-Source Voltage		± 16	
TJ	Operating Junction and	-55 to + 150	°C
T <sub>STG</sub>	Storage Temperature Range	-95 (0 + 150	

## **Thermal Resistance**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③		100	°C/W
$R_{\theta,JA}$	Junction-to-Ambient (t < 10s) @		99	C/VV



## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient		0.06		V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
D	Static Drain-to-Source On-Resistance		98	116	mΩ	$V_{GS} = 4.5V, I_D = 2.2A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance		78	92	11122	$V_{GS} = 10V, I_D = 2.7A$
$V_{GS(th)}$	Gate Threshold Voltage	1.0		2.5	V	$V_{DS} = V_{GS}$ , $I_D = 25\mu A$
	Drain-to-Source Leakage Current			20	μA	$V_{DS} = 60V, V_{GS} = 0V$
I <sub>DSS</sub>	Dialii-to-Source Leakage Current			250	μΑ	$V_{DS} = 60V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
ı	Gate-to-Source Forward Leakage			100	nA	V <sub>GS</sub> = 16V
I <sub>GSS</sub>	Gate-to-Source Reverse Leakage			-100	IIA	V <sub>GS</sub> = -16V
$R_G$	Internal Gate Resistance		1.6		Ω	
gfs	Forward Trans conductance	7.6			S	$V_{DS} = 25V, I_{D} = 2.7A$
$Q_g$	Total Gate Charge		2.5			I <sub>D</sub> = 2.7A
$Q_{gs}$	Gate-to-Source Charge		0.7		nC	$V_{DS} = 30V$
$Q_{gd}$	Gate-to-Drain ('Miller') Charge		1.3			V <sub>GS</sub> = 4.5V ②
$t_{d(on)}$	Turn-On Delay Time		5.4			V <sub>DD</sub> = 30V2
t <sub>r</sub>	Rise Time		6.3		]	I <sub>D</sub> = 1.0A
$t_{d(off)}$	Turn-Off Delay Time		6.8		ns	$R_G = 6.8\Omega$
t <sub>f</sub>	Fall Time		4.2			$V_{GS} = 4.5V$
C <sub>iss</sub>	Input Capacitance		290			V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance		37		pF	$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance		21			f = 1.0MHz

#### Source-Drain Ratings and Characteristics

Source-Drain Ratings and Characteristics						
	Parameter	Min.	Тур.	Max.	Units	Conditions
Is	Continuous Source Current (Body Diode)			1.6		MOSFET symbol showing the
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①			11		integral reverse p-n junction diode.
$V_{SD}$	Diode Forward Voltage			1.3	٧	$T_J = 25^{\circ}C, I_S = 2.7A, V_{GS} = 0V ②$
t <sub>rr</sub>	Reverse Recovery Time		14	21	ns	$T_J = 25^{\circ}C$ , $V_R = 30V$ , $I_F = 1.6A$
$Q_{rr}$	Reverse Recovery Charge		13	20	nC	di/dt = 100A/µs ②

#### Notes:

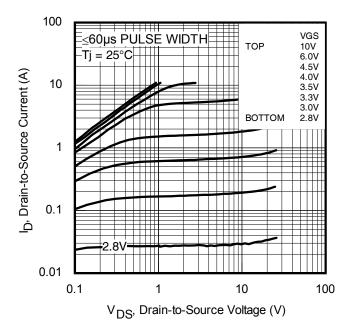
① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400μs; duty cycle ≤ 2%.
 ③ Surface mounted on 1 in square Cu board

Refer to application note #AN-994.

2016-12-20





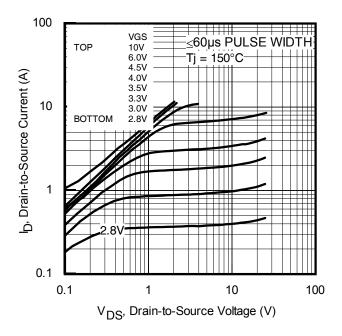


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

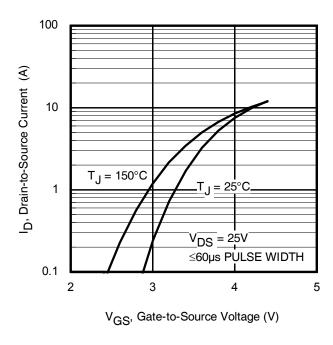
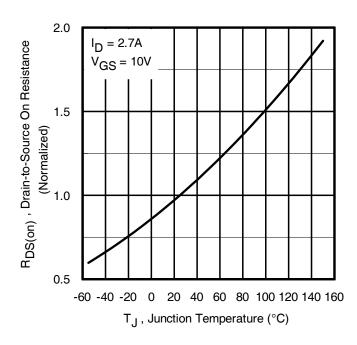
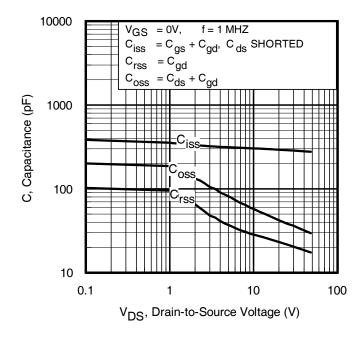


Fig. 3 Typical Transfer Characteristics

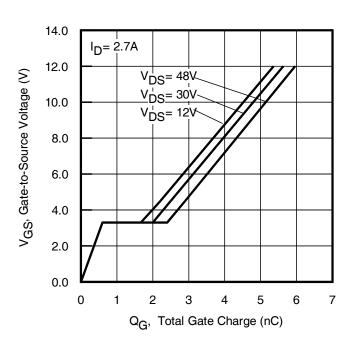


**Fig. 4** Normalized On-Resistance vs. Temperature





**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

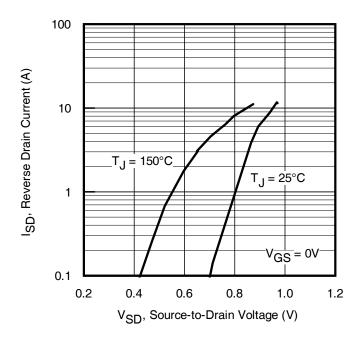


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

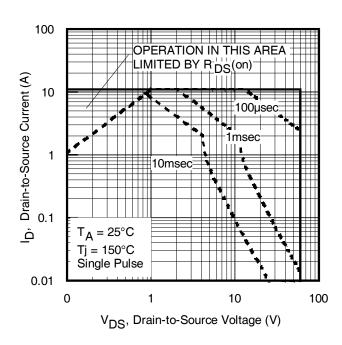


Fig 8. Maximum Safe Operating Area

4



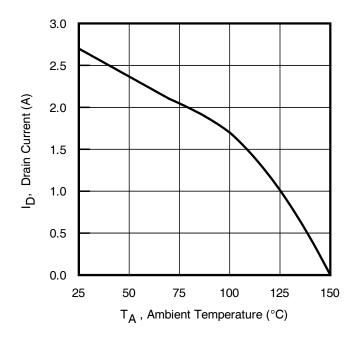


Fig 9. Maximum Drain Current vs. Case Temperature

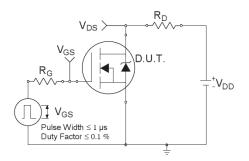


Fig 10a. Switching Time Test Circuit

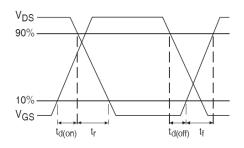


Fig 10b. Switching Time Waveforms

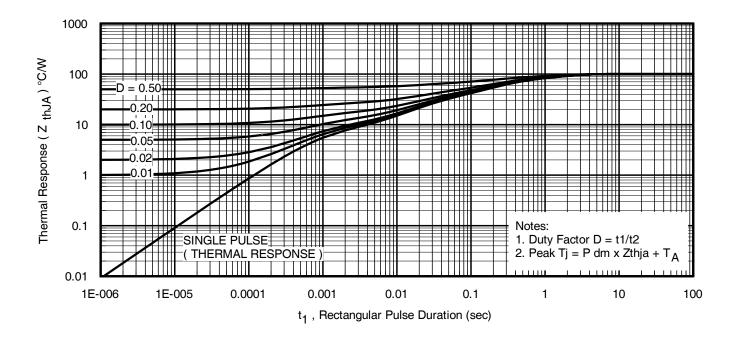
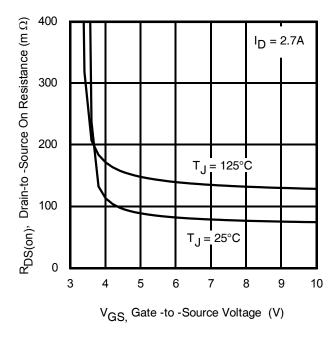
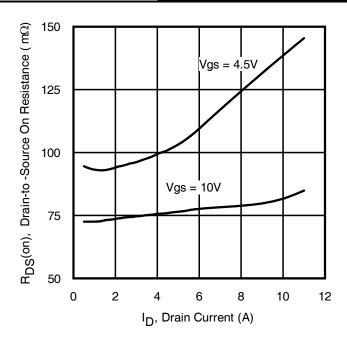


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





**Fig 12.** Typical On-Resistance Vs. Gate Voltage



**Fig 13.** Typical On-Resistance Vs. Drain Current

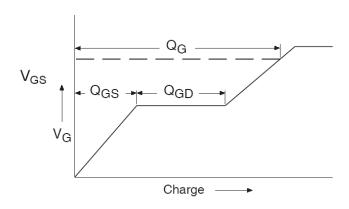


Fig 14a. Basic Gate Charge Waveform

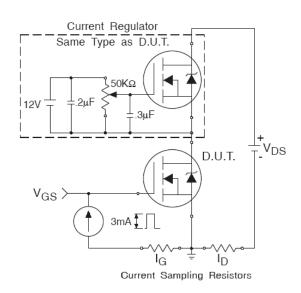
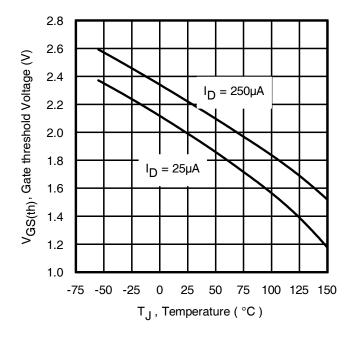


Fig 14b. Gate Charge Test Circuit





**Fig 15.** Typical Threshold Voltage Vs. Junction Temperature

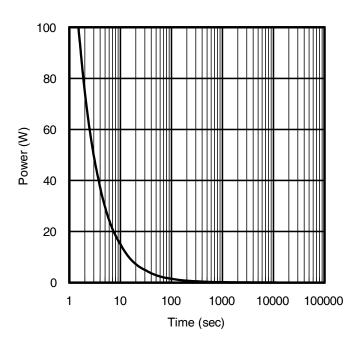
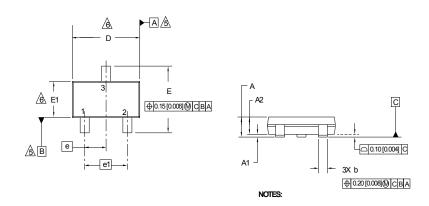


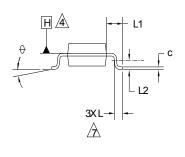
Fig 16. Typical Power Vs. Time



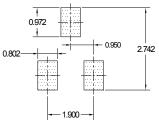
#### Micro3™ (SOT-23) Package Outline (Dimensions are shown in millimeters (inches))



DIMENSIONS						
SYMBOL	MILLIM	ETERS	INC	HES		
STIVECE	MIN	MAX	MIN	MAX		
Α	0.89	1.12	0.035	0.044		
A1	0.01	0.10	0.0004	0.004		
A2	0.88	1.02	0.035	0.040		
b	0.30	0.50	0.012	0.020		
С	0.08	0.20	0.003	0.008		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E1	1.20	1.40	0.047	0.055		
е	0.95	BSC	0.037	BSC		
e1	1.90	BSC	0.075	BSC		
L	0.40	0.60	0.016	0.024		
L1	0.54	REF	0.021	REF		
L2	0.25	BSC	0.010	BSC		
0	0	8	0	8		



# Recommended Footprint

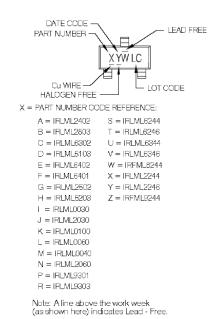


#### NOTES:

- 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
- 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3. CONTROLLING DIMENSION: MILLIMETER. ADATUM PLANE HIS LOCATED AT THE MOLD PARTING LINE.
- ADATUM A AND B TO BE DETERMINED AT DATUM PLANE H
  DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD FLASH, MOLD PROTRUSIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM [0.010 INCH] PER SIDE.
- ⚠ DIMENSION LIS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE. 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO 236 AB.

## Micro3™ (SOT-23/TO-236AB) Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001



## DATE CODE MARKING INSTRUCTIONS

WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YE	AR	Υ	WORK WEEK	W	
2011	2001	1	01	Α	
2012	2002	2	02	В	
2013	2003	3	03	0	
2014	2004	4	04	D	
2015	2005	5			
2016	2006	6			
2017	2007	7			
2018	2008	8	1	1	
2019	2009	9	7	•	
2020	2010	0	24	X	
			25	Y	
			26	7	

WW = (27-52) IF PRECEDED BY A LETTER

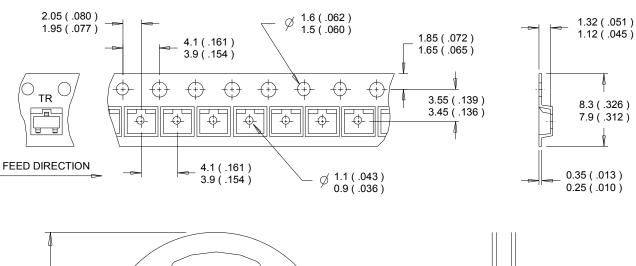
YE	AR	Υ	WORK WEEK	W
2011	2001	Α	27	Α
2012	2002	В	28	В
2013	2003	С	29	C
2014	2004	D	30	D
2015	2005	Ε		
2016	2006	F		
2017	2007	G		
2018	2008	Н		1
2019	2009	J	7	•
2020	2010	K	50	X
			51	Y
			50	7

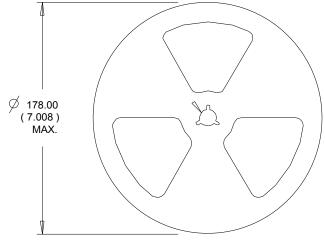
Note: For the most current drawing please refer to Infineon's web site www.infineon.com

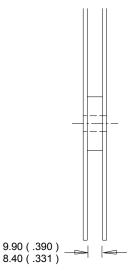
2016-12-20



### Micro3™ Tape & Reel Information (Dimensions are shown in millimeters (inches))







#### NOTES:

- 1. CONTROLLING DIMENSION: MILLIMETER.
- 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to Infineon's web site www.infineon.com

2016-12-20



#### **Qualification Information**

Qualification Level	Consumer (per JEDEC JESD47F) <sup>†</sup>				
Moisture Sensitivity Level	MSL1 (per JEDEC J-STD-020D) †				
RoHS Compliant	Yes				

† Applicable version of JEDEC standard at the time of product release.

#### **Revision History**

Date	Comments
12/20/16	<ul> <li>Changed datasheet with Infineon logo - all pages.</li> <li>Removed typo "Industrial" on Feature and Benefits Table on page1.</li> <li>Corrected typo for Igss test condition from "V<sub>GS</sub> = 20V" to "V<sub>GS</sub> = 16V" on page 2.</li> </ul>

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